Abstract Submitted
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Doping effects in Bi_2Se_3 and Bi_2Te_3 topological insulators[1]
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[2]Hor *et al.* PRB **79** 195208 (09)
[3]Ibid.
[4]Checkelsky *et al.* arXiv:0909.1840
[5]Hor *et al.* arXiv:0909.2890.

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